

Sunday, September 27

9:00-12:15 Tutrial Session: Future of quantum computer - Quantum technology on the move -
 13:00-17:10 Short Course A: Recent advances in organic electronics
 13:00-17:25 Short Course B: 5G evolution and beyond

Monday, September 28

8:45-12:45 Opening & Plenary Sessions & Award Ceremony

Room A	Room B	Room C	Room D	Room E	Room F	Room G	Room H	Room I	Room J	Room K	Room L
14:00-15:30 Area1 & 2 A-1:Ferroelectric Devices I		14:00-15:30 C-1:Advanced Interconnects & 3D Integration I	14:00-15:30 D-1:Ultrawide-Bandgap Devices	14:00-15:15 E-1:Novel Laser Structures	14:00-15:30 F-1:Battery/Fuel Cell/Energy Harvesting	14:15-15:30 G-1:Organic Light-emitting Materials and Devices	14:00-15:30 H-1:Growth and Synthesis 1	14:00-15:30 I-1:Spintronics I	14:00-15:15 J-1:2D Materials and Structures	14:00-15:30 K-1:Group IV Materials	
Break											
	16:00-17:45 Area1 & 2 B-2:Ferroelectric Devices II	16:00-17:45 C-2:Advanced Interconnects & 3D Integration II	16:00-17:45 D-2:GaN Vertical Device Technologies	16:00-17:30 E-2:New Materials for Light Emitting Devices	16:00-17:45 F-2:Thermoelectric Devices	16:00-17:45 G-2:Organic Photovoltaics	16:00-17:45 H-2:Growth and Synthesis 2	16:00-17:45 I-2:Spintronics II and Quantum Sensing	16:00-17:30 J-2:Flexible and Printable Device Applications	16:00-17:30 K-2:Group IV Materials	

Tuesday, September 29

Room A	Room B	Room C	Room D	Room E	Room F	Room G	Room H	Room I	Room J	Room K	Room L
9:00-10:30 A-3:3D Integration and Device Characterization			9:00-10:30 D-3:Innovative RF Device and Circuit Technologies for Beyond 5G			10:00-10:30 G-3:Functional Materials and Devices (1)	9:00-10:30 H-3:Characterization 1				
Break											
11:00-12:30 A-4:CMOS-based Sensors		11:00-12:30 C-4:Advanced Interconnects & 3D Integration III	11:00-12:30 D-4:SiC Device Technologies	11:00-12:00 E-4:III-V Integrated Semiconductor Lasers		11:00-12:00 G-4:Functional Materials and Devices (2)	11:00-12:30 H-4:Characterization 2	11:00-12:30 I-4:Superconducting Qubit	11:00-12:30 J-4:Novel Optoelectronic Device Applications	11:00-12:00 K-4:III-V, Nitride, and Related Compound Semiconductors	
Lunch											
14:00-15:30 A-5:Advanced CMOS Technology		14:00-15:15 Area3 & 12 C-5:Advanced Integration Technology	14:00-15:30 D-5:III-V Device Technologies			14:00-15:30 G-5:Organic Transistors	14:00-15:15 H-5:Characterization 3	14:00-15:30 I-5:Neuromorphic and Novel Functional Device	14:00-15:00 J-5:Advanced Si Thin Film Technologies	14:00-15:15 K-5:III-V, Nitride, and Related Compound Semiconductors	
Break											
16:00-17:45 A-6:Process Technology		16:00-17:30 C-6:Advanced Imager and Related Photonic Device Technologies	16:00-17:45 D-6:SiC MOS Devices		16:00-18:00 F-6:Perovskite Solar Cell	16:00-17:15 G-6:Organic Carrier Transport Materials	16:00-17:30 H-6:Characterization 4	16:00-17:45 I-6:Semiconductor Qubit	16:00-17:45 J-6:Oxide Semiconductor Materials and Devices		

Wednesday, September 30

Room A	Room B	Room C	Room D	Room E	Room F	Room G	Room H	Room I	Room J	Room K	Room L
9:30-10:30 Area1 & 12 A-7:Energy-Efficient Integrated Technologies	9:00-10:15 B-7:Emerging Memories and Application		9:00-10:30 D-7:Wide-Bandgap High-Speed Devices				9:00-10:30 H-7:Device Applications 1				
Break											
	11:00-12:00 Area2 & 12 B-8:Advanced Non-Volatile Memory Devices, Circuits and Systems		11:00-12:30 D-8:Advanced Si Power Devices	11:00-12:15 E-8:New Optical Devices for Sensing and Quantum Technologies		11:00-12:00 G-8:Biосensors and Biointerfaces	11:00-12:15 H-8:Device Applications 2			11:00-12:15 K-8:Oxide Materials	
Lunch											
	14:00-15:30 B-9:Memory Computing	14:00-15:30 C-9:MEMS & Displays	14:00-15:30 D-9:Characterization and Simulation for Wide-Bandgap Devices	14:00-15:45 E-9:Integrated Optical Modulator	14:00-15:30 F-9:Compound Solar Cell	14:00-15:30 G-9:Optical Device for Bio-Imaging	14:00-15:00 H-9:Device Applications 3			14:00-15:30 K-9:Nanomaterials	14:00-15:30 L-9: Integrated Circuits for IoT and Sensing
Break											
	16:00-17:45 B-10:ReRAM and Non-Volatile Memories		16:00-18:00 D-10:GaN Device Technologies	16:00-17:15 E-10:Advanced Integrated Photonics	16:00-17:45 F-10:Silicon Solar Cell	16:00-17:15 G-10:FET-Based Techniques for Biosensing	16:00-17:45 H-10:Device Applications 4			16:00-18:15 K-10:Advanced Crystal Growth and Synthesis	16:00-17:15 L-10:Processor Related Circuits and Image Sensors

Area Scope	Description
	Area 1: Advanced CMOS: Material Fundamentals / Process Science / Device Physics
	Area 2: Advanced and Emerging Memories / New Applications
	Area 3: Interconnect / 3D Integrations / MEMS
	Area 4: Power / High-speed Devices and Materials
	Area 5: Photonics: Devices / Integration / Related Technology
	Area 6: Photovoltaic / Energy Harvesting / Battery-related Technology

Area Scope	Description
	Area 7: Organic / Molecular / Bio-electronics
	Area 8: Low Dimensional Devices and Materials
	Area 9: Novel Functional / Quantum / Spintronic Devices and Materials
	Area 10: Thin Film Electronics: Oxide / Non-single Crystalline / Novel Process
	Area 11: Advanced Materials: Synthesis / Crystal Growth / Characterization
	Area 12: Advanced Circuits / Systems Interacting with Innovative Devices and Materials